

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	715	(wet oxidation) same activ\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 12:45
L7	26	(wet oxidation) same activat\$3 with (oxygen or O2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 12:49
L9	10	("20030162372" "20030207556" "20030224618" "20040147136" "20040166632").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 12:59
L20	141	(dummy wafer adj5 (silicon or silicon oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 14:34
L21	42	(vertical same furnace same batch) and oxid\$5 and ((dummy or test or monitor\$3) adj3 (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 14:51
L23	296	(wafer boat) same (dummy or test or monitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 15:23
L24	58	23 and (dummy or test or monitor) with (silicon or silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 15:24
L25	8	23 and (dummy or test or monitor) with (silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 15:52
L26	610	((dummy or test or monitor) with (wafer or substrate)) with (silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 15:54

L27	127	((dummy or test or monitor) adj3 (wafer or substrate)) with (silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 15:54
L28	57298	(wet or thermal) adj3 oxidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 16:05
L29	1534	28 and ((dummy or monitor) with (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 16:05
L30	235	28 and ((dummy or monitor) with (substrate or wafer) same (silicon oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 16:06
L31	4	28 and (dummy wafer with silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 16:08
L32	16	28 and (dummy wafer same silicon oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/10 16:08
S1	4	("20020014483" "6211094").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 12:19
S2	3	427/248.1.cds. and (dummy wafer) and ((plural\$5 or multi\$3) with heat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 13:41
S3	17	427/248.1.cds. and (dummy wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 13:42
S4	34	("3627569" "5131752" "5318632" "5800616" "6054181"). PN. OR ("6211094"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2008/05/20 13:45

S5	10	dummy wafer and loading effect	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:09
S6	0	427/248.1.ccls. and ((dummy or monitor\$3) adj2 (wafer or substrate)) and (loading effect)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:39
S7	31	((dummy or monitor\$3) adj2 (wafer or substrate)) and (loading effect)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:39
S8	24	427/248.1.ccls. and (silica or silicon oxide) and (wafer adj5 (plural \$5 or multi\$3))	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:44
S9	79	(silica or silicon oxide same (CVD or (thermal adj2 process\$3))) and (wafer adj5 (dummy or monitor\$3) same oxide)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:56
S10	38	(dummy same oxide) and loading effect and (silica or silicon oxide)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 14:57
S11	38	(wafer boat) and (thickness with measur \$5) and (temperature with (set\$5 or correct \$5)) and (silica or silicon oxide)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 15:15
S12	6	(wafer boat) and ((plural \$5 or multi\$3) adj5 heat \$3) same zone and (thickness with measur \$5)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 15:24
S13	13	(wafer boat) and loading effect	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 15:47
S14	34	(dummy with wafer with oxide) and (silicon adj3 (wafer or substrate)) and (measur \$5 with thickness)	US_PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 15:55

S15	2	(heat treatment or thermal processing or oxidation treatment) and (vertical with react \$4) and (dummy with wafer with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 16:07
S16	43	(heat treatment or thermal processing or oxidation treatment) and (vertical with react \$4) and (dummy with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 16:08
S17	16	S16 and (thick\$5 with (measur\$5 or control \$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 16:16
S18	12	(dummy with wafer) and (temperature with set\$3) and (temperature with correct\$3) and recipe	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 16:21
S19	4	118/712,715.cds. and (dummy adj3 wafer) and (thick\$5 adj3 measur\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/05/20 16:48
S20	2	"6329643".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 08:16
S21	10837	((wafer or substrate) with (oxide)) and ((wafer or substrate) with (bare or silicon)) and ((control\$3 or adjust\$5 or set\$3) adj3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 08:48
S22	32	((wafer or substrate) with (oxide) same dummy) and ((wafer or substrate) with (bare or silicon) same dummy) and ((control\$3 or adjust\$5 or set\$3) adj3 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 08:49

S23	240	batch and wafer boat and (plural\$3 with heat \$3) and (temperature with (adjust\$5 or set\$3 or control\$3 or correct \$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 08:55
S24	4	S23 and load\$3 adj2 effect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 08:55
S25	60	S23 and dummy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 09:01
S26	2	"6121114".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 09:14
S27	2	"6869892".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 09:16
S28	102	(loading effect) and batch and silicon and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 09:41
S29	34	("3627569" "5131752" "5318632" "5800616" "6054181"). PN. OR ("6211094"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2008/06/05 09:46
S30	2	"6730885".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 09:59
S31	9	("4605161" "5112641" "5517591" "5517594" "5593608" "5616264" "5622639" "6306764"). PN. OR ("6730885"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2008/06/05 09:59

S32	28	suzuki-f.in. and heat treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:04
S33	9	(batch with heat with treat\$4) and ((different or oxide or bare or blank) with (dummy or monitoring) with (wafer or substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:12
S34	10	(batch with vertical) and ((different or oxide or bare or blank) with (dummy or monitoring) with (wafer or substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:14
S35	9	(temperature with (correct\$3)) and (thickness with measur \$5) and ((dummy or monitor\$3) with (wafer or substrate) same (oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:21
S36	788	(thickness with measur \$3 same thin film) and (temperature with (adjust\$3 or set\$3 or correct\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:35
S37	3	S36 and (vertical with furnace) and ((plural\$5 or multi\$3) with (heat \$3 or zone))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:37
S38	11	S36 and (vertical with furnace)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:38
S39	54	"118".clas. and (vertical with furnace) and ((dummy or monitoring) with (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:52
S40	106	"427".clas. and (silicon oxide) and dummy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:56

S41	47	(silicon oxide or silicon dioxide or silica) and (vertical with furnace) and (dummy with (wafer or substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 10:59
S42	411	427/9.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 11:01
S43	8	S42 and dummy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 11:01
S44	103	S42 and (temperature with (adjust\$3 or control \$3 or set\$5 or correct \$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 11:03
S45	260	(wafer boat) and (thickness with (control \$3 or measur\$5)) and (temperature with (adjust\$5 or set\$3 or correct\$3 or control\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 11:58
S46	113	(dummy wafer same (silicon oxide or silicon dioxide or SiO2 or bare silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 12:15
S47	26	(dummy with oxide) and (dummy with bare)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 14:19
S48	13	(loading effect) and (wafer boat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/06/05 14:24

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